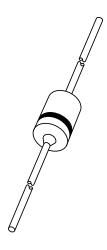
## DISCRETE SEMICONDUCTORS

## DATA SHEET



# **BZX55 series**Voltage regulator diodes

Product specification Supersedes data of April 1992 File under Discrete Semiconductors, SC01 1996 Apr 26





## **BZX55** series

#### **FEATURES**

- Total power dissipation: max. 500 mW
- Tolerance series: ±5%
- Working voltage range: nom. 2.4 to 75 V (E24 range)
- Non-repetitive peak reverse power dissipation: max. 40 W.

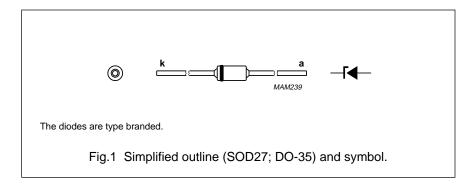
#### **APPLICATIONS**

Low voltage stabilizers or voltage references.

#### **DESCRIPTION**

Low-power voltage regulator diodes in hermetically sealed leaded glass SOD27 (DO-35) packages.

The diodes are available in the normalized E24  $\pm5\%$  tolerance range. The series consists of 37 types with nominal working voltages from 2.4 to 75 V (BZX55-C2V4 to BZX55-C75).



#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I <sub>F</sub>	continuous forward current		_	250	mA
I <sub>ZSM</sub>	non-repetitive peak reverse current	$t_p$ = 100 μs; square wave; $T_j$ = 25 °C prior to surge		Table type"	
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 50 °C; note 1	_	400	mW
		T <sub>amb</sub> = 50 °C; note 2	_	500	mW
P <sub>ZSM</sub>	non-repetitive peak reverse power dissipation	$t_p$ = 100 μs; square wave; $T_j$ = 25 °C prior to surge	_	40	W
		$t_p$ = 8.3 ms; square wave; $T_j \le 150$ °C prior to surge	_	30	W
T <sub>stg</sub>	storage temperature		-65	+200	°C
Tj	junction temperature		_	200	°C

#### **Notes**

- 1. Device mounted on a printed circuit-board without metallization pad; lead length max.
- 2. Tie-point temperature ≤ 50 °C; lead length 8 mm.

#### **ELECTRICAL CHARACTERISTICS**

### **Total series**

 $T_i = 25$  °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 100 mA; see Fig.4	ı	1.0	V

## BZX55 series

Per type  $T_j = 25 \,^{\circ}\text{C}$ ; unless otherwise specified.

	WOR	WORKING	DIFFER RESIS	DIFFERENTIAL RESISTANCE	TEMP. COEFF. Sz (mV/K)	TEST	DIODE CAP. C <sub>d</sub> (pF)	REVER REVE	REVERSE CURRENT at REVERSE VOLTAGE	T at	NON-REPETITIVE PEAK REVERSE
BZYKK	$V_{z}(V)$	3	rdif	r <sub>dif</sub> (Ω)	at Iztest	I <sub>Ztest</sub> (mA)	at f = 1 MHz;		I <sub>R</sub> (μΑ)		CURRENT
CXXX	at .	at I <sub>Ztest</sub>	at Iz	at I <sub>Ztest</sub>	see Figs 5 and 6		at V <sub>R</sub> = 0 V	at $T_{\rm j} = 25 ^{\circ}{\rm C}$	at Tj = 150 °C	> S	$_{ m LSM}$ (A) at $_{ m t_p}$ = 100 $_{ m \mu S}$ ; $_{ m Tamb}$ = 25 $^{\circ}$ C
•	M N	MAX.	MAX.	MAX.	TYP.		MAX.	MAX.	MAX.	Ē	MAX.
2V4	2.28	2.56	009	85	-1.8	5	450	20	100	1.0	6.0
2V7	2.5	2.9	009	85	-1.9	5	450	10	20	1.0	0.9
370	2.8	3.2	009	85	-2.1	2	450	4	40	1.0	0.9
3V3	3.1	3.5	009	85	-2.2	5	450	2	40	1.0	6.0
376	3.4	3.8	009	85	-2.4	2	450	2	40	1.0	0.9
3/9	3.7	4.1	009	85	-2.4	5	450	2	40	1.0	6.0
4V3	4.0	4.6	009	80	-2.4	2	450	-	20	1.0	0.9
4V7	4.4	2.0	009	02	4.1-	9	300	0.5	10	1.0	0.9
5V1	4.8	5.4	220	20	-0.8	5	300	0.1	2	1.0	6.0
576	5.2	0.9	450	30	1.6	2	300	0.1	2	1.0	0.9
6V2	5.8	9.9	200	10	2.2	9	200	0.1	2	2.0	0.9
6V8	6.4	7.2	150	8	3.0	2	200	0.1	2	3.0	0.9
7/5	7.0	7.9	20	7	3.8	2	150	0.1	2	2.0	4.0
8V2	2.7	8.7	09	2	4.5	9	150	0.1	2	6.15	4.0
9V1	8.5	9.6	20	10	5.5	2	150	0.1	2	8.9	3.0
10	9.4	10.6	70	15	6.5	2	90	0.1	2	7.5	3.0
11	10.4	11.6	02	20	7.7	9	92	0.1	2	8.25	2.5
12	11.4	12.7	06	20	8.4	9	58	0.1	2	0.6	2.5
13	12.4	14.1	110	26	9.8	2	80	0.1	2	9.75	2.5
15	13.8	15.6	110	30	11.3	9	92	0.1	2	11.25	2.0
16	15.3	17.1	170	40	12.8	2	22	0.1	2	12.0	1.5
18	16.8	19.1	170	20	14.4	2	02	0.1	2	13.5	1.5
20	18.8	21.2	220	22	16.0	5	09	0.1	2	15.0	1.5

## BZX55 series

			<u> </u>	I	ı				ı						ı	<u> </u>
NON-REPETITIVE PEAK REVERSE CURRENT	$_{LSM}$ (A) at $t_{p}$ = 100 μs; $_{Tamb}$ = 25 $^{\circ}$ C	MAX.	1.25	1.25	1.0	1.0	6.0	8.0	7.0	9.0	9.0	0.4	6.0	6.0	0.25	0.2
T at SE	, S	<u> </u>	16.5	18.0	20.25	22.25	24.75	27.0	29.25	32.25	35.25	38.25	42.0	46.5	51.0	56.25
REVERSE CURRENT at REVERSE VOLTAGE I <sub>R</sub> (µA)	at at $T_j = 25  ^{\circ}\text{C}$ $T_j = 150  ^{\circ}\text{C}$	MAX.	2	2	2	2	2	2	2	2	2	2	2	2	2	2
REVER REVE	at T <sub>j</sub> = 25 °C	MAX.	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1	0.1
DIODE CAP. $C_d$ (pF) at $f = 1$ MHz;	at $V_R = 0 V$	MAX.	09	55	50	20	45	45	45	40	40	40	40	35	35	35
TEST CURRENT I <sub>Ztest</sub> (mA)			5	5	5	2	2	2	2.5	2.5	2.5	2.5	2.5	2.5	2.5	2.5
TEMP. COEFF. S <sub>2</sub> (mV/K) at I <sub>2test</sub>	see Figs 5 and 6	TYP.	18.7	20.4	22.9	27.0	29.7	32.4	35.1	38.7	44.0	49.0	55.0	62.0	70.0	78.0
DIFFERENTIAL RESISTANCE rdif (\O)	at I <sub>Ztest</sub>	MAX.	55	80	80	80	80	80	06	06	110	125	135	150	200	250
	at Iz	MAX.	220	220	220	220	220	220	200	009	700	200	1000	1000	1000	1500
WORKING VOLTAGE V <sub>Z</sub> (V)	at I <sub>Ztest</sub>	MAX.	23.3	25.6	28.9	32.0	35.0	38.0	41.0	46.0	50.0	54.0	0.09	0.99	72.0	79.0
WOR VOL	at T	× N N	20.8	22.8	25.1	28.0	31.0	34.0	37.0	40.0	44.0	48.0	52.0	28.0	64.0	70.0
27466	CXXX		22	24	27	30	33	36	39	43	47	51	99	62	89	75

Note

1. For BZX55-C2V4 up to C36  $I_Z$  = 1 mA; for C39 up to C75  $I_Z$  = 0.5 mA.

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## Voltage regulator diodes

BZX55 series

## THERMAL CHARACTERISTICS

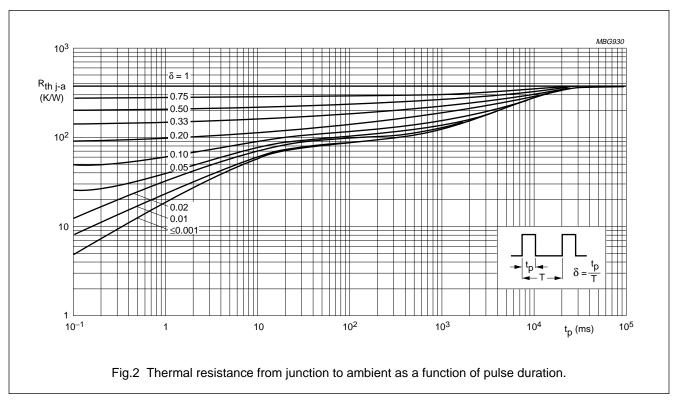
SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-tp</sub>	thermal resistance from junction to tie-point	lead length 8 mm	300	K/W
R <sub>th j-a</sub>	thermal resistance from junction to ambient	lead length max.; see Fig.2 and note 1	380	K/W

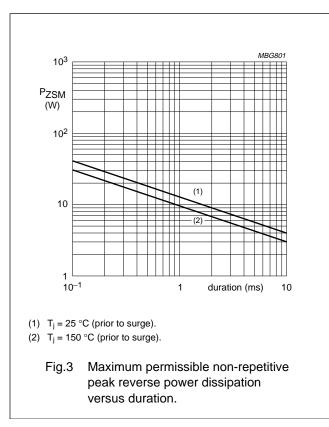
## Note

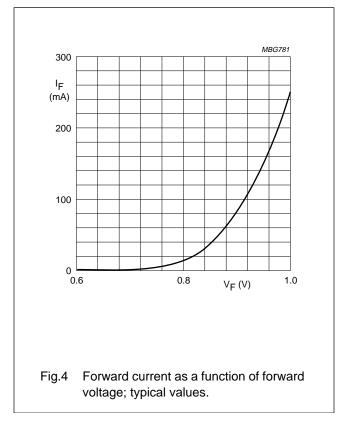
1. Device mounted on a printed circuit-board without metallization pad.

## BZX55 series

#### **GRAPHICAL DATA**



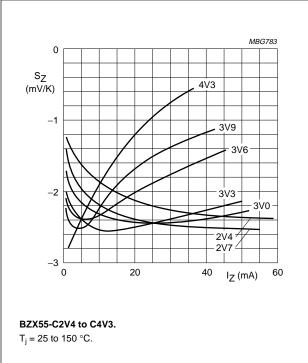




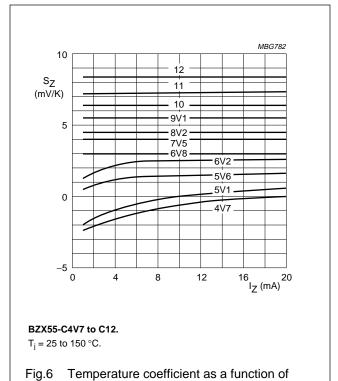
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## Voltage regulator diodes

## BZX55 series



ig.5 Temperature coefficient as a function of working current; typical values.



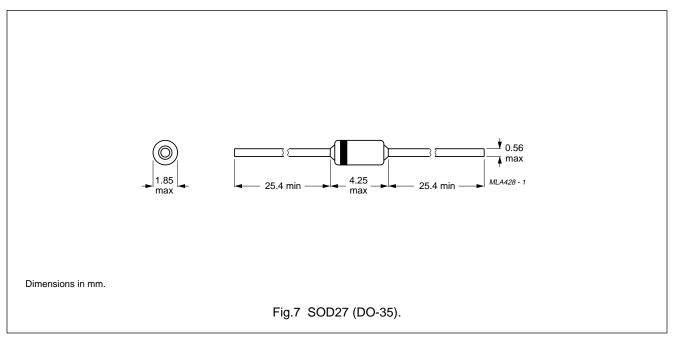
working current; typical values.

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## Voltage regulator diodes

BZX55 series

#### **PACKAGE OUTLINE**



#### **DEFINITIONS**

Data sheet status							
Objective specification This data sheet contains target or goal specifications for product development.							
Preliminary specification	Preliminary specification This data sheet contains preliminary data; supplementary data may be published later.						
Product specification	Product specification This data sheet contains final product specifications.						
Limiting values							
more of the limiting values m of the device at these or at a	accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or may cause permanent damage to the device. These are stress ratings only and operation any other conditions above those given in the Characteristics sections of the specification imiting values for extended periods may affect device reliability.						
Application information							
Where application information	on is given, it is advisory and does not form part of the specification.						

## LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.